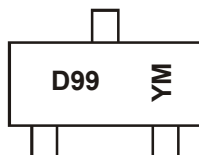


## Marking Information



D99= Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: I = 2021)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2008	.....	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	V	.....	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Drain Current (Note 5) $V_{GS} = -10V$	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	$I_D$	-3.8 -2.9	A
Pulsed Drain Current (Note 6)			$I_{DM}$	-11	A

## Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	$P_D$	1.08	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	115	$^\circ\text{C/W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-800	nA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-1.0	—	-2.1	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	65	m $\Omega$	$V_{GS} = -10V, I_D = -3.8A$
				99		$V_{GS} = -4.5V, I_D = -3.0A$
Forward Transfer Admittance	$ Y_{fs} $	—	3.6	—	S	$V_{DS} = -5V, I_D = -2.7A$
Diode Forward Voltage (Note 6)	$V_{SD}$	—	—	-1.26	V	$V_{GS} = 0V, I_S = -2.7A$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	563	—	pF	$V_{DS} = -25V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	48	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	41	—	pF	
Gate Resistance	$R_G$	—	10.3	—	$\Omega$	$V_{GS} = 0V, V_{DS} = 0V, f = 1MHz$
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Total Gate Charge	$Q_g$	—	5.2	—	nC	$V_{DS} = -15V, V_{GS} = -4.5V,$ $I_D = -3.8A$
		—	11	—		$V_{DS} = -15V, V_{GS} = -10V,$ $I_D = -3.8A$
Gate-Source Charge	$Q_{gs}$	—	1.7	—		
Gate-Drain Charge	$Q_{gd}$	—	1.9	—	ns	$V_{DS} = -15V, V_{GS} = -10V,$ $I_D = -1A, R_G = 6.0\Omega$
Turn-On Delay Time	$t_{d(on)}$	—	4.8	—		
Rise Time	$t_r$	—	5.0	—		
Turn-Off Delay Time	$t_{d(off)}$	—	31	—		
Fall Time	$t_f$	—	15	—		

- Notes:
- Device mounted on FR-4 PCB on 2 oz., 0.5 in.<sup>2</sup> copper pads and  $t \leq 5$  sec.
  - Pulse width  $\leq 10\mu s$ , Duty Cycle  $\leq 1\%$ .
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

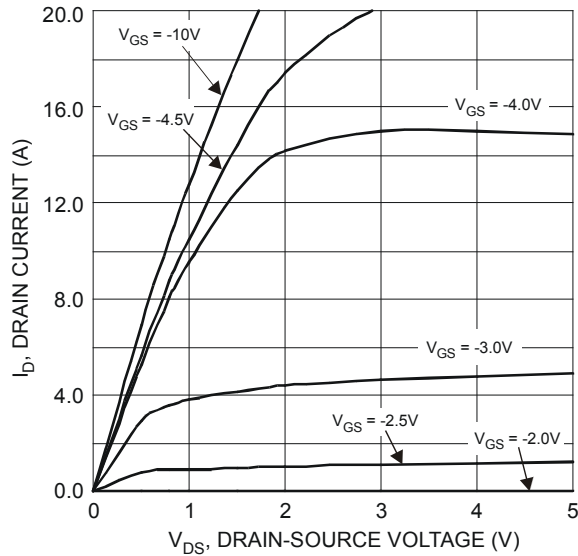


Figure 1 Typical Output Characteristics

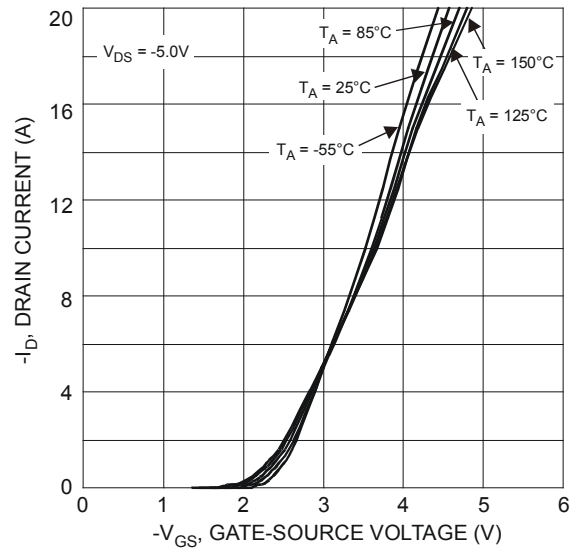


Figure 2 Typical Transfer Characteristics

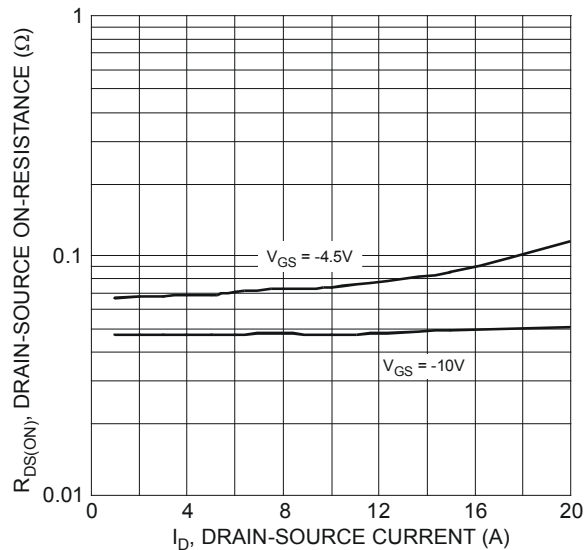


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

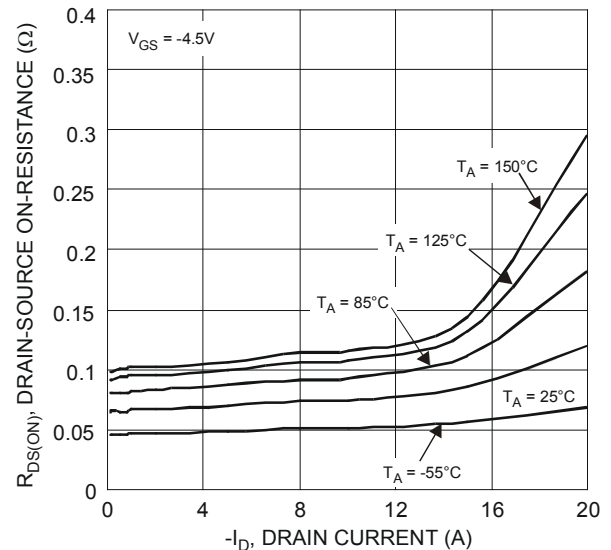


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

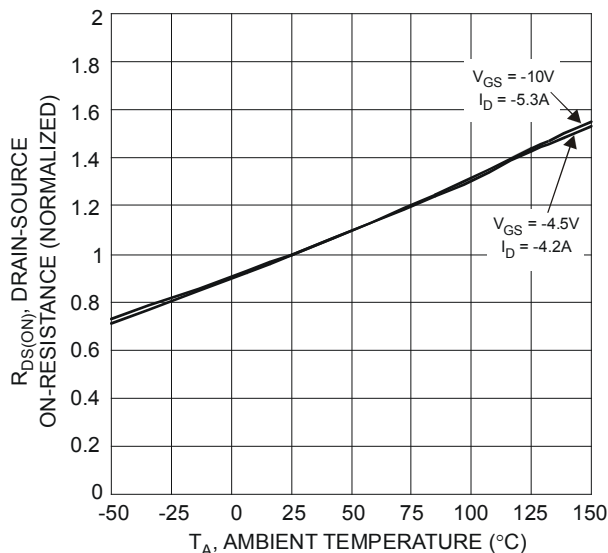


Figure 5 On-Resistance Variation with Temperature

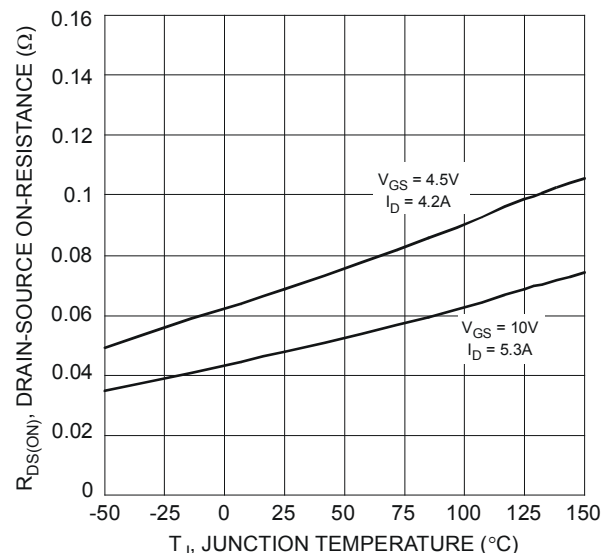


Figure 6 On-Resistance Variation with Temperature

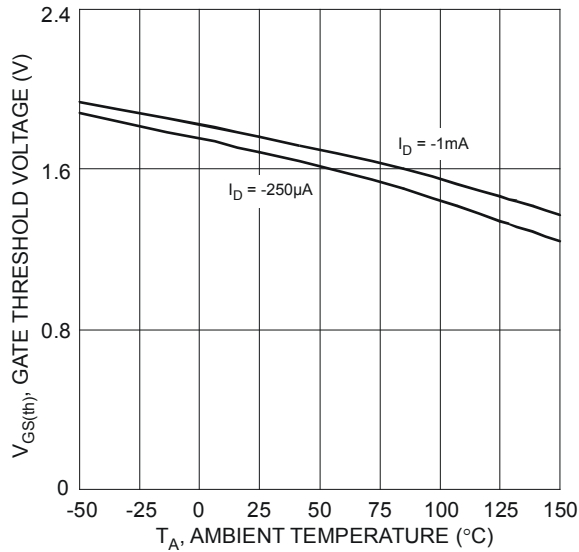


Figure 7 Gate Threshold Variation vs. Ambient Temperature

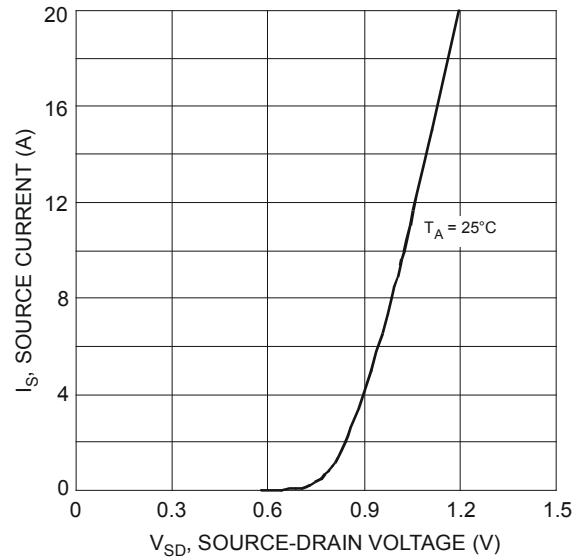


Figure 8 Diode Forward Voltage vs. Current

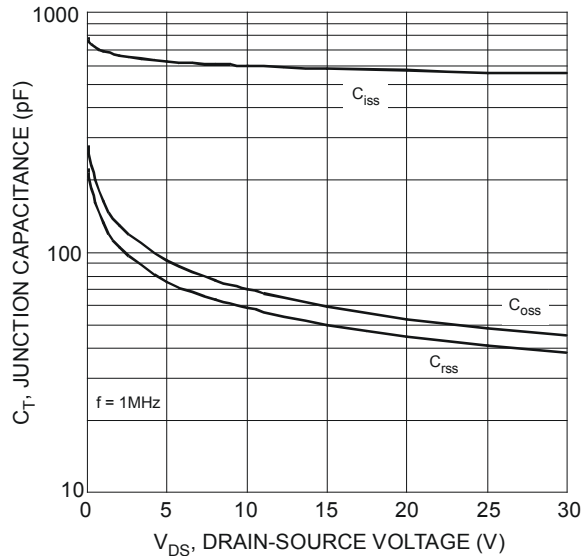


Figure 9 Typical Junction Capacitance

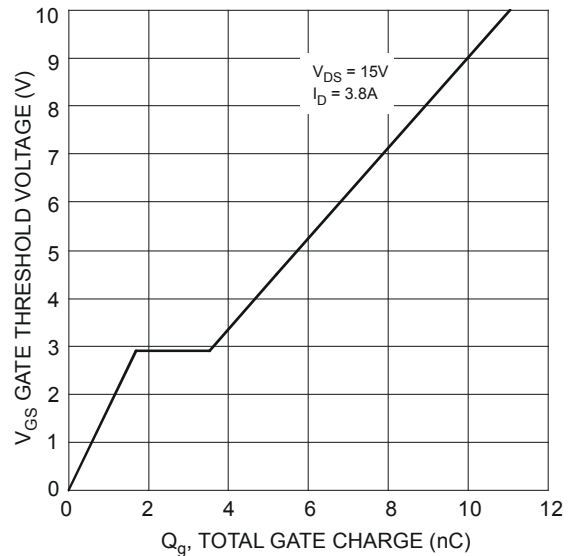
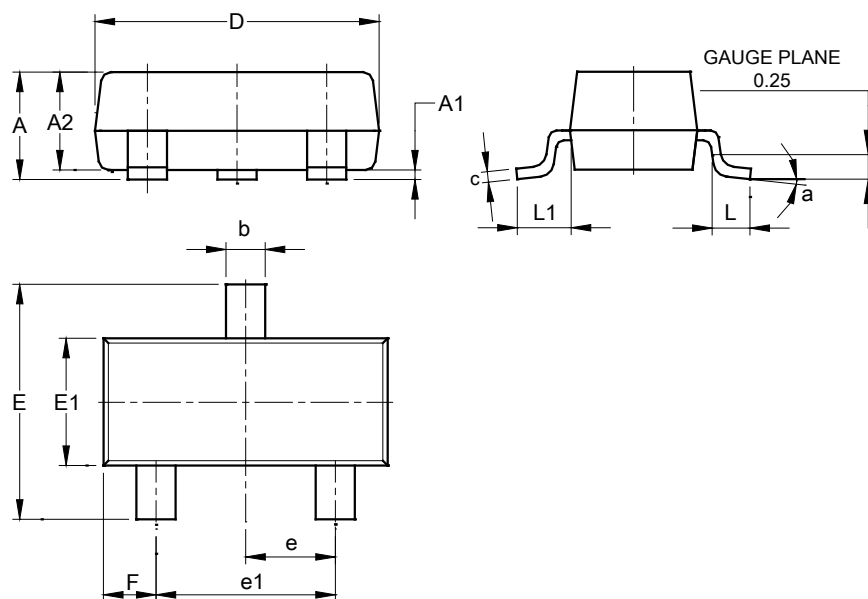


Figure 10 Gate Charge

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23 (Standard)

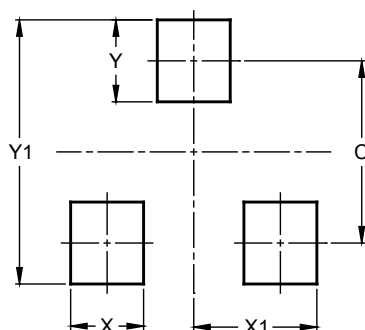


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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